

Study of structural, mechanical and electronic properties of the 2H-NbSe₂ alloy using density functional theory approach

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1. Introduction

The layered transition metal dichalcogenide 2H-NbSe₂ is of considerable interest due to its metallic conductivity, superconducting properties, and potential applications in nanoelectronics [1, 2]. Understanding the relationship between its mechanical and electronic properties is essential for strain-engineered functional materials.

2. Methodology

In this work, the structural, mechanical, and electronic properties of 2H-NbSe₂ were investigated using density functional theory (DFT) as implemented in the Quantum Espresso package. The exchange–correlation effects were treated within the generalized gradient approximation (GGA). A plane-wave basis set and periodic boundary conditions were employed.

3. Results and discussion

The optimized lattice parameter was found to be $a = 3.445 \text{ \AA}$, which is in good agreement with available experimental data [1]. The calculated elastic constants (C_{11} , C_{12} , C_{13} , C_{33} , C_{44}) satisfy the mechanical stability criteria for hexagonal crystals. The derived bulk, shear, and Young's moduli indicate moderate stiffness of the material. The Pugh ratio $B/G = 1.18$ suggests a brittle mechanical behavior under ambient conditions, consistent with the layered nature of the compound.

Compound	C_{11}	C_{12}	C_{13}	C_{33}	C_{44}
2H-NbSe ₂	150	42	18	55	5,5

Table 1. Calculated Elastic Constants (C_{11} , C_{12} , C_{13} , C_{33} and C_{44}) in Gpa for 2H-NbSe₂

The effect of small symmetric displacements of Se atoms ($\pm 1\%$) was analyzed. These deformations lead to noticeable changes in the shear modulus and longitudinal stiffness, indicating a pronounced sensitivity of the mechanical response to local atomic distortions.

Electronic structure calculations confirm the metallic nature of 2H-NbSe₂. The density of states near the Fermi level is dominated by Nb d-states. Variations in the interlayer spacing affect the width and position of the Nb d-band near the Fermi level, demonstrating a coupling between mechanical deformation and electronic properties.

The obtained results highlight the interplay between structure, mechanical response, and electronic behavior in 2H-NbSe₂. This coupling suggests the possibility of tuning electronic properties by controlled strain, which is of interest for nanoelectronic and strain-engineered applications. The results are consistent with previously reported theoretical and experimental studies of layered transition metal dichalcogenides [1–4].

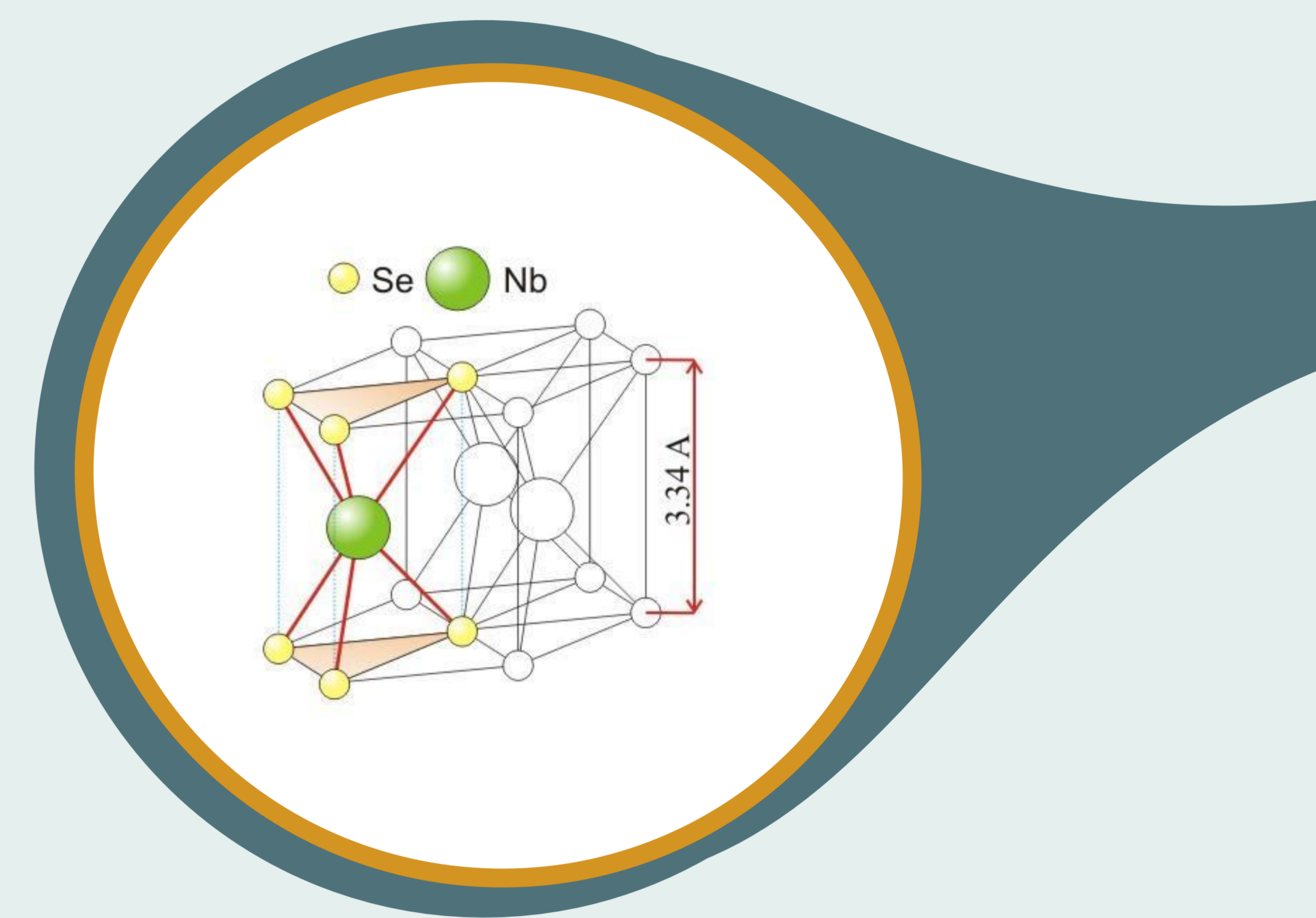


Fig. 1. Crystal structure of the 2H-NbSe₂

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